

## Supporting Information

# Single-Layer Graphene Oxide Sheet: A Novel Substrate for Dip-Pen Nanolithography

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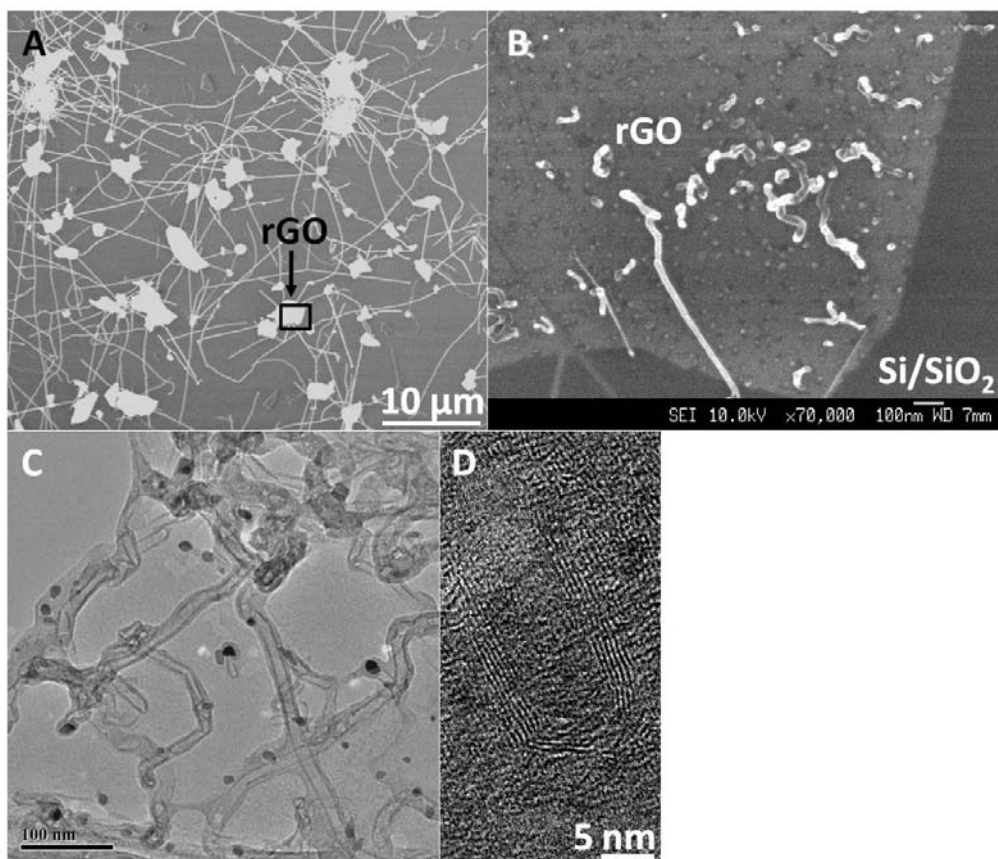
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In order to characterize the CNTs grown on GO, the following experiments were carried out. The GO substrate was prepared by adsorption of GO sheets on (3-aminopropyl) - triethoxysilane (APTES)-modified  $\text{SiO}_2$  substrate. After 0.2 mM  $\text{CoCl}_2$  methanolic solution was spin-coated on the prepared GO substrate at 2,000 rpm, the substrate was subjected to the same CVD conditions as mentioned in the main text. TEM sample was prepared by a polymer transfer technique.<sup>[1]</sup> By using this transfer technique, it is easy to distinguish the areas with or without rGO based on the typical selected area of electron diffraction (SAED) pattern of rGO in TEM.



**Figure S1.** (A) SEM image shows lots of SWCNTs grew on  $\text{SiO}_2$ , which were catalyzed by Co NPs obtained by reduction of the spin-coated  $\text{CoCl}_2$ . (B) Magnified SEM image of the box shown in (A). Some fiber-like structures were observed on rGO. (C) TEM and

(D) HRTEM images of fiber-like structures, confirming that those fiber-like structures are MWCNTs with a diameter of ~ 15 nm.

**Reference:**

- [1] A. Reina, H. Son, L. Jiao, B. Fan, M. S. Dresselhaus, Z. Liu, J. Kong, *J. Phys. Chem. C* **2008**, *112*, 17741.